

L1
and

a third chamber capable of taking said substrate out of said multi-chamber system after depositing said gate insulating film.

L2
86. (Amended) A multi-chamber system comprising:

a first chamber for irradiating a laser light to a semiconductor film formed over a substrate;

a means for introducing an oxidizing atmosphere into said first chamber;

a second chamber for depositing a gate insulating film on said semiconductor film;

a third chamber capable of taking said substrate out of said multi-chamber system after depositing said gate insulating film; and

a means for transporting said substrate among said first, second and third chambers.

L3
92. (Amended) A multi-chamber system comprising:

a first chamber for irradiating a laser light to a semiconductor film formed over a substrate;

a means for introducing an oxidizing atmosphere into said first chamber;

a second chamber for depositing a gate insulating film; and

a third chamber for putting said substrate in said multi-chamber system and for taking said substrate out of said multi-chamber system,

wherein said multi-chamber system is capable of depositing said gate insulating film on said semiconductor film irradiated with said laser light.

L4
98. (Amended) A multi-chamber system comprising:

a first chamber for irradiating a laser light to a semiconductor film formed over a

substrate;

a means for introducing an oxidizing atmosphere into said first chamber;
a second chamber for depositing a gate insulating film;
a third chamber for putting said substrate in said multi-chamber system and for taking
said substrate out of said multi-chamber system; and
a means for transporting said substrate among said first, second and third chambers,
wherein said multi-chamber system is capable of depositing said gate insulating film
on said semiconductor film irradiated with said laser light.

Please add new claims 136-153 as follows:

f4
--136. (New) A multi-chamber system according to claim 80 wherein said means
for introducing said oxidizing gas is a gas intake valve.

f5
137. (New) A multi-chamber system according to claim 86 wherein said means
for introducing said oxidizing gas is a gas intake valve.

138. (New) A multi-chamber system according to claim 92 wherein said means
for introducing said oxidizing gas is a gas intake valve.

139. (New) A multi-chamber system according to claim 98 wherein said means
for introducing said oxidizing gas is a gas intake valve.

140. (New) A multi-chamber system comprising:

a first chamber for irradiating a laser light to a semiconductor film formed over a

substrate;

a means for introducing an oxidizing atmosphere into said first chamber;
a second chamber for depositing an insulating film on said semiconductor film; and
a third chamber capable of taking said substrate out of said multi-chamber system.

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Pmt.*
141. (New) A multi-chamber system according to claim 140 wherein said second chamber is selected from the group consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

142. (New) A multi-chamber system according to claim 141 wherein a silicon oxide film is formed by one of said apparatus.

143. (New) A multi-chamber system according to claim 140 wherein said laser comprises an excimer laser or a YAG laser.

144. (New) A multi-chamber system according to claim 140 wherein said laser light has a rectangular shape on an irradiating surface.

145. (New) A multi-chamber system according to claim 140 wherein said oxidizing atmosphere comprises oxygen.

146. (New) A multi-chamber system according to claim 140 wherein said means for introducing said oxidizing gas is a gas intake valve.

147. (New) A multi-chamber system comprising:
a first chamber for irradiating a laser light to a semiconductor film formed over a substrate;
a means for introducing an oxidizing atmosphere into said first chamber;
a second chamber for depositing an insulating film on said semiconductor film; and
a third chamber for putting said substrate in said multi-chamber system and for taking said substrate out of said multi-chamber system.

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Cont.*
148. (New) A multi-chamber system according to claim 147 wherein said second chamber is selected from the group consisting of a plasma CVD apparatus, a low pressure CVD apparatus, an atmospheric pressure CVD apparatus and a sputtering film formation apparatus.

149. (New) A multi-chamber system according to claim 148 wherein a silicon oxide film is formed by one of said apparatus.

150. (New) A multi-chamber system according to claim 147 wherein said laser comprises an excimer laser or a YAG laser.

151. (New) A multi-chamber system according to claim 147 wherein said laser light has a rectangular shape on an irradiating surface.

152. (New) A multi-chamber system according to claim 147 wherein said oxidizing atmosphere comprises oxygen.